Medium power transistor (–60V, –1A) 2SA2091S

● Features

- 1) High speed switching. (Tf: Typ.: 30ns at Ic = -1A)
- 2) Low saturation voltage, typically
 - (Typ.: -200mV at Ic = -0.5A, I_B = -50mA)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SC5879S

Applications

Small signal low frequency amplifier High speed switching

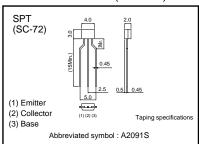
●Structure

PNP Silicon epitaxial planar transistor

Packaging specifications

	Package	Taping	
Туре	Code	TP	
	Basic ordering unit (pieces)	5000	
2SA2091S		0	

●External dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Collector-base voltage		V _{CBO}	-60	V	
Collector-emitter voltage		Vceo	-60	V	
Emitter-base voltage		Vево	-6	V	
Collector current	DC	lc	-1.0	А	
	Pulsed	Іср	-2.0	A *	
Power dissipation		Pc	300	mW	
Junction temperature		Tj	150	°C	
Range of storage temperature		Tstg	-55 to 150	°C	

^{*}Pw=100ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
Collector-emitter breakdown voltage	BVceo	-60	-	-	V	Ic=-1mA	
Collector-base breakdown voltage	ВУсво	-60	-	_	V	Ic=-100μA	
Emitter-base breakdown voltage	ВVево	-6	-	-	V	IE= -100μA	
Collector cut-off current	Ісво	_	-	-1.0	μΑ	VcB= -40V	
Emitter cut-off current	ІЕВО	_	-	-1.0	μΑ	V _{EB} = -4V	
Collector-emitter saturation voltage	VCE (sat)	-	-200	-500	mV	Ic= -500mA	
						I _B = -50mA	
DC current gain	hfE	120	-	270	_	Vce=-2V	
		120				Ic=-100mA	
Transition frequency	fτ	-	- 300	_	MHz	Vc=-10V *1	
						IE=100mA	
						f=10MHz	
Corrector output capacitance	Соь				pF	VcB= -10V	
		_	15	_		IE=0mA	
						f=1MHz	
Turn-on time	Ton	-	30	-	ns	Ic=-1.0A *2	
Storage time	Tstg	-	100	-	ns	I _{В1} = –100mA I _{В2} =100mA	
Fall time	Tf	_	30	-	ns	Vcc≒-25V	

●hFE RANK

Q	
120–270	

•Electrical characteristic curves

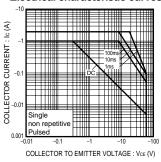


Fig.1 Safe Operating Area

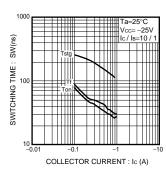


Fig.2 Switching Time

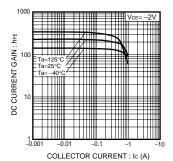


Fig.3 DC Current Gain vs. Collector Current (I)

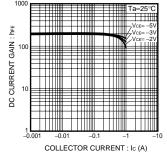


Fig.4 DC Current Gain vs. Collector Current (II)

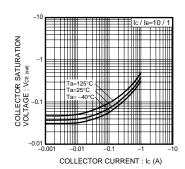


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

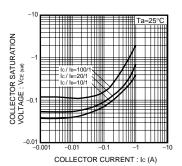


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

2/3



^{*1} Non repetitive pulse *2 See Switching charactaristics measurement circuits

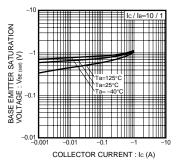


Fig.7 Base-Emitter Saturation Voltage vs. Collecter Current

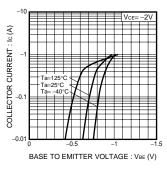


Fig.8 Grounded Emitter
Propagation Characteristics

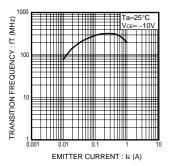


Fig.9 Transition Frequency

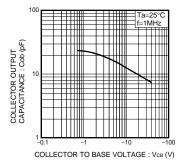
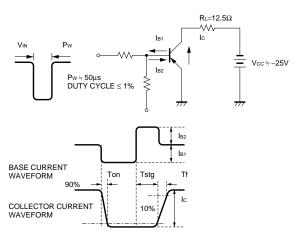


Fig.10 Collector Output Capacitance

Switching characteristics measurement circuits



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